Erratum

Characterization of MOVPE-Grown GaAs Layers by C-V Analysis

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Due to a printing error the figure caption to Fig. 2 was incorrect and should read

Fig. 2. The capacitance C_{sc} as a function of the surface potential v_s in the SCL of n -type GaAs epitaxial layer; $N_{sd} - N_{sa} = 1 \times 10^{14} \text{ cm}^{-3}$, $N_{dd} [\text{cm}^{-3}] = (A: 0, B: 5 \times 10^{13}, C: 5 \times 10^{14}, D: 5 \times 10^{15}, E: 5 \times 10^{16})$